

## CENTRAL INTELLIGENCE AGENCY

## INFORMATION REPORT

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COUNTRY	East Germany	REPORT NO.	<input type="text"/>
SUBJECT	Successful Transistor Development at Werk Carl von Ossietzky (Dralowid)	DATE DISTR.	13 May 1954
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THE SOURCE EVALUATIONS IN THIS REPORT ARE DEFINITIVE.  
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SOURCE: 

1. Dr. Matthias Falter of the Carl von Ossietzky Werk (formerly Dralowid) in Teltow, after having succeeded in developing transistors of the point-contact type in a relatively short time, was invited by the Ministry for Post and Telecommunications to demonstrate his transistors to experts of the Ministry. He did so in early January 1954. The transistors were found satisfactory in every respect. Dr. Falter's success was immediately reported to the Russian authorities. Subsequently, a Russian inspection team appeared at Falter's plant and tested the transistors there. The Russians were quite surprised at Falter's work, especially since he had accomplished it in such a short time.
2. On about 20 January 1954, a Russian commission, headed by a civilian who identified himself as Major Ivanov<sup>1</sup> visited the development department of the Werk fuer Fernmeldewesen HF (formerly OSW) in Berlin-Oberschoeneweide and seized all transistors either completed or in development, all germanium supplies, measurement devices and tools used for the development. At the same time, the management was notified that effective immediately all funds for transistor development at the HF Werk were withdrawn. Ivanov accused leading specialists who had been engaged in transistor development, mainly Dr. Walter Rohde and Dr. Boehm (fnu), of sabotage on the grounds that they had not been able to complete the development successfully after more than two years. Dr. Rohde was immediately transferred to another HF department; Dr. Boehm was ordered to assist the Russians in winding up transistor development at the enterprise.
3. One day after the incident at the HF Werk, Dr. Falter of Dralowid was notified by the Russians that in the future transistor development for the Russians will be carried out exclusively in the Carl von Ossietzky Werk.
1.  Comment.  a Russian acceptance official Ivanov (fnu) was reported to have visited the HF Werk three times from 1951 to 1953. He was said to be stationed at Sachsenwerk Radeberg.

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